

IN THE SPECIFICATION:

Page 11, lines 21-23 should read:

Fig. 5 4e is a SEM photograph illustrating a comparison of the conventional semiconductor device and a semiconductor device according to the present invention.

Page 16, lines 3-15 should read:

Fig 5 4e is a SEM photograph illustrating a comparison of the conventional semiconductor device and a semiconductor device according to the present invention.

Referring to Fig. 5 4e, the photograph on the left shows the thickness of the nitride film formed on the bit line 33 according to the conventional method, and the photograph on the right shows the thickness of the nitride film formed on the bit line 51 of the semiconductor device according to the present invention. As shown in Fig. 5 4e, it should be noted that the thickness of the nitride film on the bit line 51 of the semiconductor device according to the present invention is thicker than that of the nitride film according to the conventional method (denoted by "p").